

GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 50 - 66 GHz

Typical Applications

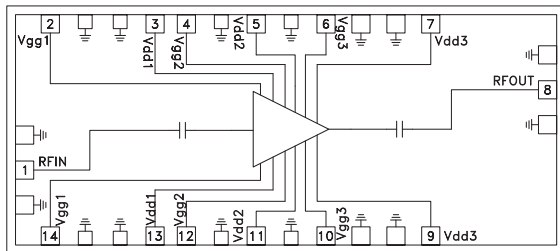
This HMC-ABH241 is ideal for:

- Short Haul / High Capacity Links
- Wireless LAN Bridges
- Military & Space

Features

- Output IP3: +25 dBm
- P1dB: +17 dBm
- Gain: 24 dB
- Supply Voltage: +5 V
- 50 Ohm Matched Input/Output
- Die Size: 3.2 x 1.42 x 0.1 mm

Functional Diagram



General Description

The HMC-ABH241 is a four stage GaAs HEMT MMIC Medium Power Amplifier which operates between 50 and 66 GHz. The HMC-ABH241 provides 24 dB of gain, and an output power of +17 dBm at 1dB compression from a +5V supply voltage. All bond pads and the die backside are Ti/Au metallized and the amplifier device is fully passivated for reliable operation. The HMC-ABH241 GaAs HEMT MMIC Medium Power Amplifier is compatible with conventional die attach methods, as well as thermocompression and thermosonic wire bonding, making it ideal for MCM and hybrid microcircuit applications. All data shown herein is measured with the chip in a 50 Ohm environment and contacted with RF probes.

Electrical Specifications, $T_A = +25^\circ \text{C}$, $V_{dd1} = V_{dd2} = V_{dd3} = 5\text{V}$, $I_{dd1} + I_{dd2} + I_{dd3} = 220\text{mA}$ [2]

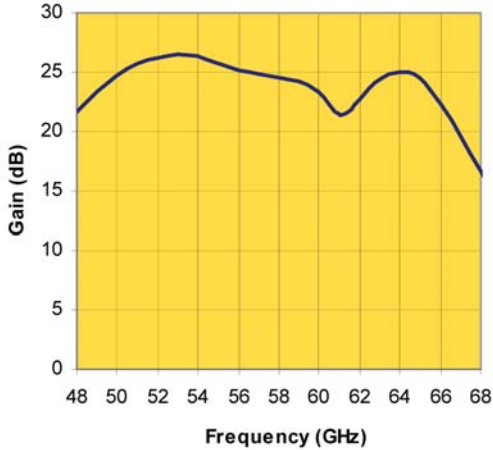
Parameter	Min.	Typ.	Max.	Units
Frequency Range		50 - 66		GHz
Gain	19	24		dB
Input Return Loss		15		dB
Output Return Loss		15		dB
Output Power for 1 dB Compression (P1dB)		17		dBm
Output Third Order Intercept (IP3)		25		dBm
Saturated Output Power (Psat)		19		dBm
Supply Current (I _{dd1} + I _{dd2} + I _{dd3})		220		mA

[1] Unless otherwise indicated, all measurements are from probed die

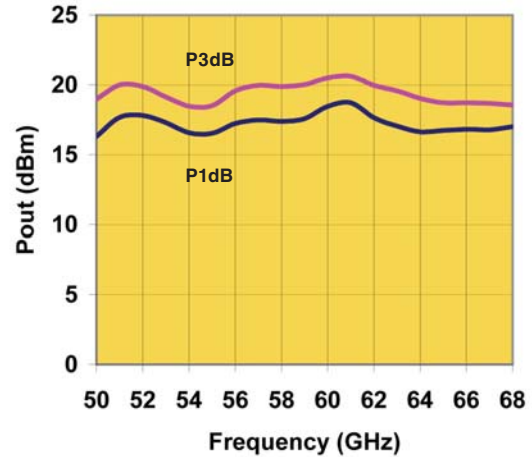
[2] Adjust V_{gg1} = V_{gg2} = V_{gg3} between -1V to +0.3V (typ -0.3V).

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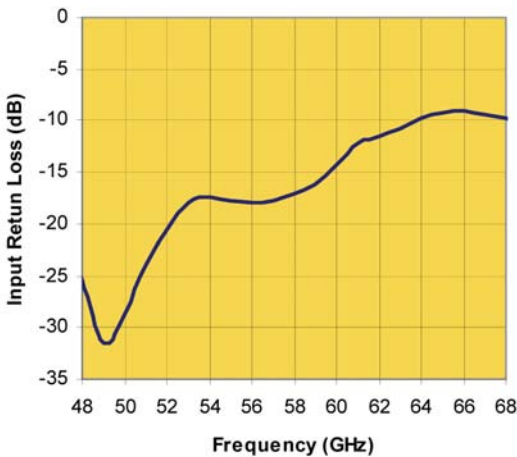
Linear Gain vs. Frequency



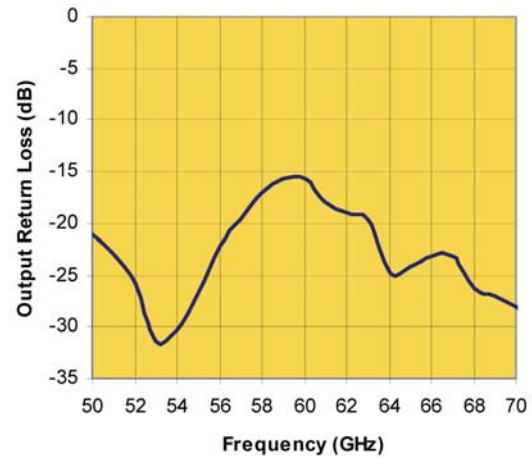
Fixtured Output Power vs. Frequency



Input Return Loss vs. Frequency



Output Return Loss vs. Frequency



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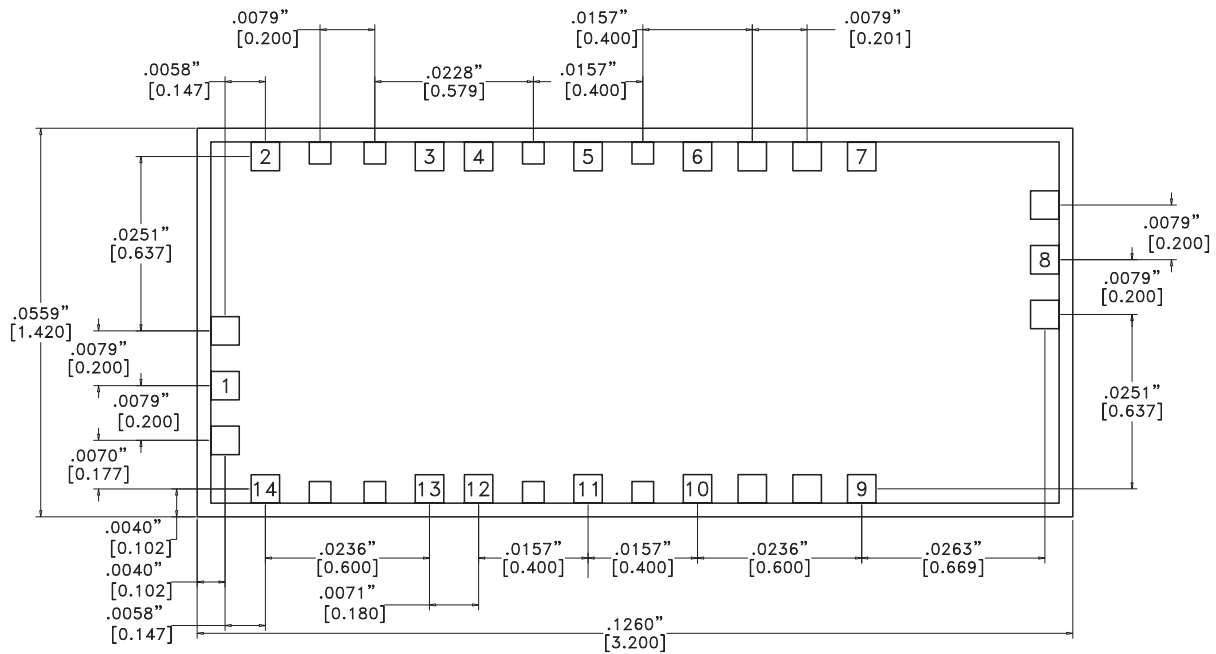
Absolute Maximum Ratings

Drain Bias Voltage	+5.5 Vdc
Gain Bias Voltage	-1 to +0.3 Vdc
RF Input Power	2 dBm
Storage Temperature	-65 °C to + 150°C
Chennel Temperature	+180 °C



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



NOTES:

1. ALL DIMENSIONS ARE IN INCHES [MM].
2. TYPICAL BOND PAD IS .004" SQUARE.
3. BACKSIDE METALLIZATION: GOLD.
4. BACKSIDE METAL IS GROUND.
5. BOND PAD METALLIZATION: GOLD.
6. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
7. OVERALL DIE SIZE $\pm .002"$